

## UNIVERSITI TUN HUSSEIN ONN MALAYSIA

## **FINAL EXAMINATION SEMESTER I SESSION 2016/2017**

**COURSE NAME** 

SEMICONDUCTOR MATERIAL

**ANALYSIS** 

**COURSE CODE** 

: BED 40702

PROGRAMME CODE : BEJ

EXAMINATION DATE : DECEMBER 2016 / JANUARY 2017

**DURATION** 

2 HOURS

INSTRUCTION

ANSWER ALL QUESTIONS

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THIS QUESTION PAPER CONSISTS OF FOUR (4) PAGES

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Q1	(a)	There are several types of bonding in solids.				
		(i)	List and explain <b>THREE</b> (3) types of bonding in solids.	(6 marks)		
		(ii)	State ONE (1) example in form of Lewis structure for each of bonding type in Q1(a)(i).	the listed		
				(3 marks)		
	(b)	Recombination process is created and eliminated in semiconductors.				
		(i)	Define the recombination process.	(3 marks)		
		(ii)	Sketch complete mechanism of direct recombination process	occurs in		
			Gallium Nitride (GaN) semiconductor compound.	(7 marks)		
	(c)	Compare TWO (2) types of thermoelectric phenomena.				
Q2	Analyze the given semiconductor elementals in form of atomic number, color, melting periodic chemical reactivity and its specific application.					
	(a)	Boron.		(5 marks)		
	(b)	Silicon.				
	(c)	Germanium.				
	(d)	Gray tin.				
	(e)	Phosphorus.		(5 marks)		
Q3	Silicon Carbide (SiC) is a chemical compound of Carbon and Silicon.					
	(a)	(i)	Illustrate the structure of SiC compound.	(3 marks)		
		(ii)	Name the shape of SiC structure.	(1 mark)		



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(b)

There are so many methods to synthesize SiC compound. Propose the method and

		provide	FIVE (5) important parameters used to synthesize SiC.		
				(6 marks)	
	(c)	Propose prepara	e THREE (3) types of characterization tools and their purtion.	pose/s in SiC	
				(6 marks)	
	(d)	Based of provide	ibed in Q3(c),		
		(i)	Color/s.		
		(ii)	Size.		
		(iii)	Shape/s.		
			Crystal structure.		
		. ,	Density (or other related property).		
				(5 marks)	
	(e)	List FO	UR (4) specific applications of SiC.		
				(4 marks)	
Q4	(a)	Crystal structure is one of the important properties in semiconductor element compounds. Describe the definition of:			
		(i) U	Unit cell.		
		(-)		(1 mark)	
		(ii) I	Lattice.		
		(11)	Sattioe.	(1 mark)	
	(b)	and name the unit cell for the listed semiconductor compounds.			
		(i) H	Boron Phosphide.		
		(-)		(7 marks)	
		(ii) (	Gallium Nitride.		
				(7 marks)	
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- (c) Gallium Nitride (GaN) is one example of direct bandgap semiconductor while Gallium Phosphide (GaP) is one example of indirect bandgap semiconductor. Both compounds are very useful in light-emitting diodes application.
  - (i) Define the direct bandgap and indirect bandgap.

(4 marks)

(ii) Sketch an E-k diagram of electron-hole recombination in GaP compound. (5 marks)

-END OF QUESTIONS -

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